

-30V P-CHANNEL Power MOSFET

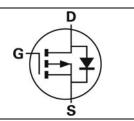
V<sub>DSS</sub>, -30V

 $R_{DS(ON)}$  ,  $9.6m\Omega$  (max.) @  $V_{GS} = -10V$   $R_{DS(ON)}$  ,  $14m\Omega$  (max.) @  $V_{GS} = -4.5V$ 

I<sub>D</sub>, -11A







## **Description**

The SG30P05S uses advanced trench technology MOSFETs to provide excellent  $R_{DS(ON)}$  and low gate charge.

The complementary Power MOSFETs may be used in H-bridge, Inverters and other applications.

#### **Features**

- · Low On-Resistance
- · Low Input Capacitance
- Low Miller Charge
- · Low Input / Output Leakage
- Pb-free lead plating; RoHS compliant

#### **Applications**

- Motor / Body Load Control
- · Automotive Systems
- Load Switch

**Ordering Information** 

Orderi	ng Code	RoHS Status	Package	Package Code	Packing	Quantity
SG3	0P05S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parame	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DS</sub>	-30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Dunin Coursest Continuous	T <sub>A</sub> =25°C	1	-11	А
Drain Current-Continuous	T <sub>A</sub> =70°C	lo lo	-9	А
Drain Current-Pulsed Note 1	<u>.</u>	I <sub>DM</sub>	-55	А
Mariana Danca Dissination	T <sub>A</sub> =25°C	D.	2	W
Maximum Power Dissipation	T <sub>A</sub> =70°C	P <sub>D</sub>	1.3	W
Avalanche Current	las	-55	А	
Avalanche Energy, L=0.1mH	Eas	151	mJ	
Storage Temperature Range	Tstg	-55 to +150	°C	
Operating Junction Temperature Range		TJ	-55 to +150	°C

**Thermal Resistance Ratings** 

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	Reja	Steady State	=	-	75	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	24	°C/W

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## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-30	-	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-1	μΑ	
Gate-Body Leakage	Igss	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250µA	-1	-1.5	-2.5	V
Drain Course On Chata Basistanas	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-15A	-	-	9.6	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =-4.5V, I <sub>DS</sub> =-7A	-	-	14	

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	3275	-	
Output Capacitance	$C_{oss}$	$V_{DS}$ =-15V, $V_{GS}$ =0V, f=1MHz	-	482	-	pF
Reverse Transfer Capacitance	Crss		-	399	-	
Forward Transconductance	gfs	V <sub>D</sub> =-5V, I <sub>D</sub> =-12A	-	25	-	S

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	$T_{d(on)}$		-	7.6	-	
Rise Time	tr	$V_{DD}$ =-15V, $V_{GS}$ =-10V, $R_{G}$ =3.3 $\Omega$ ,	-	16.9	-	
Turn-Off Delay Time	T <sub>d(off)</sub>	I <sub>D</sub> =-12A	-	74.4	-	ns
Fall Time	t <sub>f</sub>		-	41.4	-	
Total Gate Charge at -4.5V	Qg		-	31.3	-	
Gate to Source Gate Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-12A	-	10.1	-	nC
Gate to Drain "Miller" Charge	$Q_{gd}$		-	12.1	-	

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-12A	-	-	-1.2	V
Continuous Source Current	Is	\\ -\\ -0\\ Faras Current	-	-	-11	Α
Pulsed Source Current	I <sub>SM</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	-	-	-55	Α
Body Diode Reverse Recovery Time	trr	V <sub>DD</sub> =50V, I <sub>F</sub> =-12A, di/dt=100A/μs	-	19	-	ns
Body Diode Reverse Recovery Charge	Qrr	V <sub>DD</sub> =50V, I <sub>F</sub> =-12A, di/dt=100A/μs	-	9	-	nC

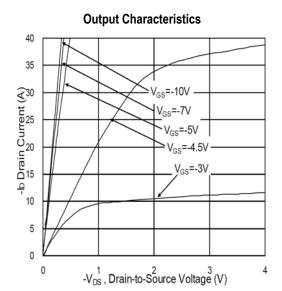
#### Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Reja is guaranteed by design while Reja is determined by the user's board design. Reja shown below for single device operation on FR-4 in still air.

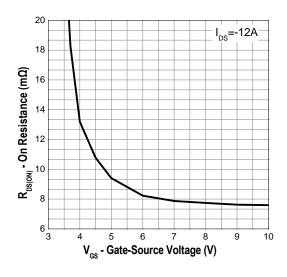


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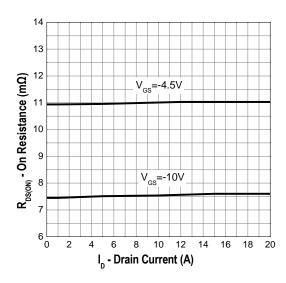
## **Typical Operating Characteristics**



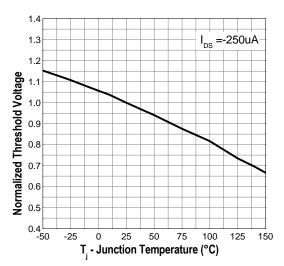
#### **Gate-Source On Resistance**



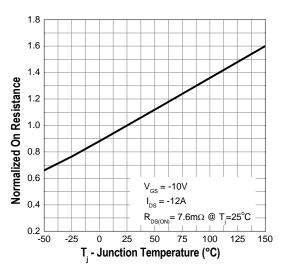
#### **Drain-Source On Resistance**



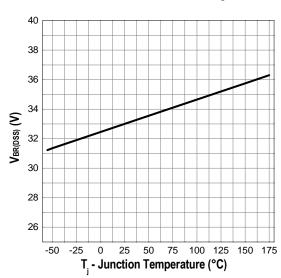
#### **Gate Threshold Voltage**



#### **Drain-Source On Resistance**



#### **Drain-source Breakdown Voltage**

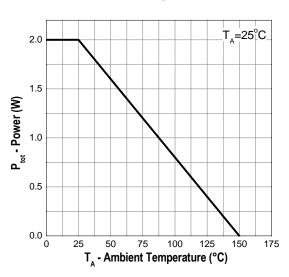




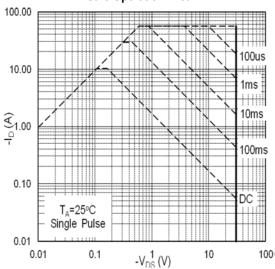
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## **Typical Operating Characteristics (Cont.)**

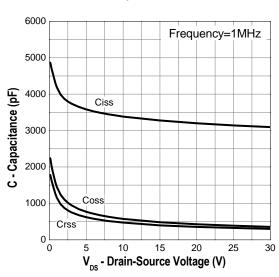
## **Power Dissipation**



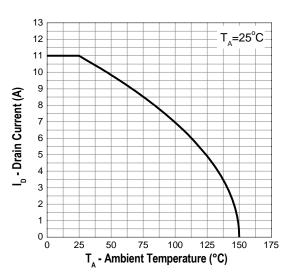
Safe Operation Area



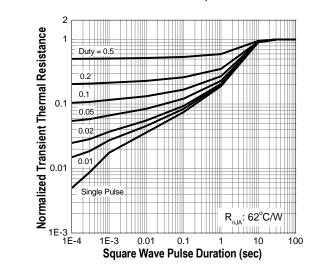
Capacitance



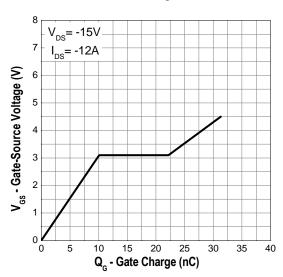
**Drain Current** 



**Transient Thermal Impedance** 



**Gate Charge** 





SG30P05S
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# **Marking Information**

SOP-8 (S)	Marking Rule
Laser Marking	Line 1 : Device Name
	SG30P05S
	Line 2 : Date Code
SG30P05S	YYMMXXX
YYMMXXX	YY: Year Code
	MM: Month Code
	XXX : Serial Number

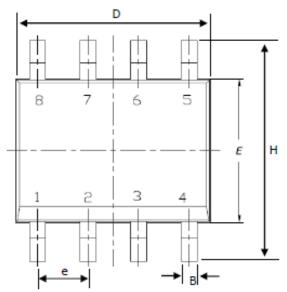




# silicongear

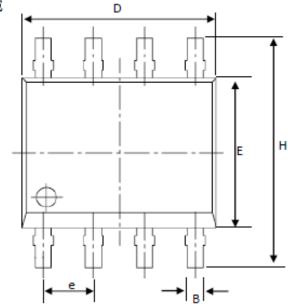
# **Package of Dimension**





Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
Е	3.80	3.90	4.00
e	1.27	1.27	1.27
Н	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00

B-TYPE





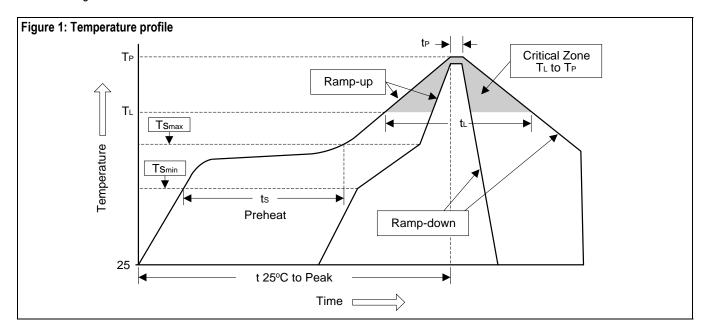
- 1. All dimension are in millimeters.
- 2. Dimension does not include burrs and mold flash/protrusions.



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## Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T <sub>L</sub>		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)	10 to 50 Sec	20 10 40 560
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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